

HCS65R160T

650V N-Channel Super Junction MOSFET

Features

- Very Low FOM ($R_{DS(on)} \times Q_g$)
- Extremely low switching loss
- Excellent stability and uniformity
- 100% Avalanche Tested

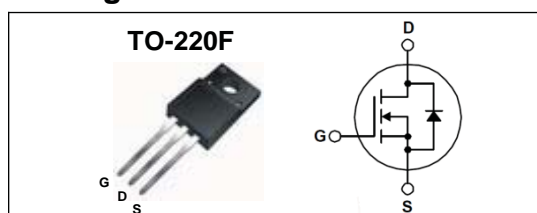
Application

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- TV power & LED Lighting Power

Key Parameters

Parameter	Value	Unit
$BV_{DSS} @ T_{j,max}$	700	V
I_D	20	A
$R_{DS(on), max}$	0.16	Ω
Q_g, Typ	41	nC

Package & Internal Circuit



Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current – Continuous ($T_C = 25^\circ\text{C}$)	20.0 *	A
	Drain Current – Continuous ($T_C = 100^\circ\text{C}$)	12.6 *	A
I_{DM}	Drain Current – Pulsed (Note 1)	60.0 *	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	640	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	34.5	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	260	$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	3.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Electrical Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

On Characteristics

V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	--	0.14	0.16	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 10, I_D = 10 \text{ A}$	--	18.8	--	S

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650 \text{ V}, V_{GS} = 0 \text{ V}$	--	--	10	μA
		$V_{DS} = 520 \text{ V}, T_J = 125^\circ\text{C}$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	--	--	± 100	nA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	--	1600	2100	pF
C_{oss}	Output Capacitance		--	225	295	pF
C_{riss}	Reverse Transfer Capacitance		--	14	18.5	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 325 \text{ V}, I_D = 20 \text{ A}, R_G = 25 \Omega$	--	48	104	ns
t_r	Turn-On Rise Time		--	108	220	ns
$t_{d(off)}$	Turn-Off Delay Time		--	176	360	ns
t_f	Turn-Off Fall Time		--	50	108	ns
Q_g	Total Gate Charge	$V_{DS} = 520 \text{ V}, I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}$	--	41	53	nC
Q_{gs}	Gate-Source Charge		--	8	--	nC
Q_{gd}	Gate-Drain Charge		--	15	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I_S	Continuous Source-Drain Diode Forward Current	--	--	20	A	
I_{SM}	Pulsed Source-Drain Diode Forward Current	--	--	60		
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 20 \text{ A}, V_{GS} = 0 \text{ V}$	--	--	1.2	V
t_{rr}	Reverse Recovery Time	$I_S = 20 \text{ A}, V_{GS} = 0 \text{ V}, di_F/dt = 100 \text{ A}/\mu\text{s}$	--	460	--	ns
Q_{rr}	Reverse Recovery Charge		--	8.2	--	μC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $I_{AS}=6\text{A}, V_{DD}=50\text{V}, R_G=25\Omega, \text{Starting } T_J=25^\circ\text{C}$
3. Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Characteristics

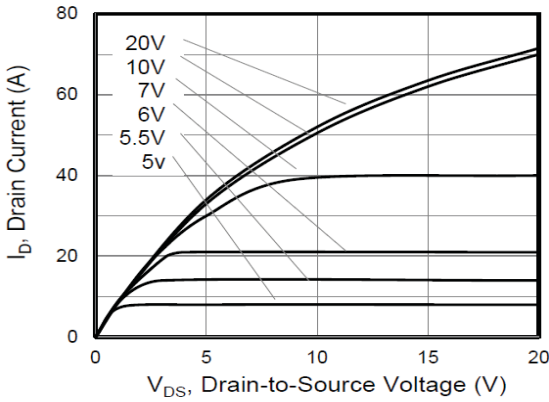


Figure 1. On Region Characteristics

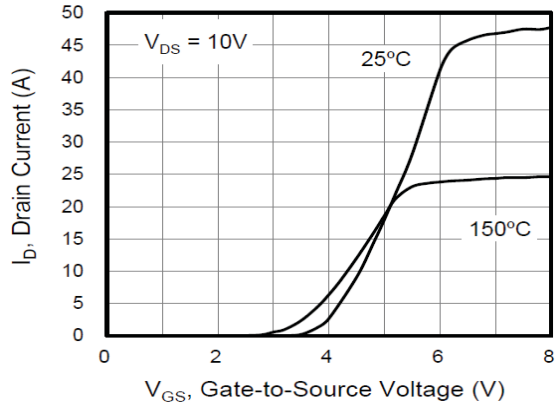


Figure 2. Transfer Characteristics

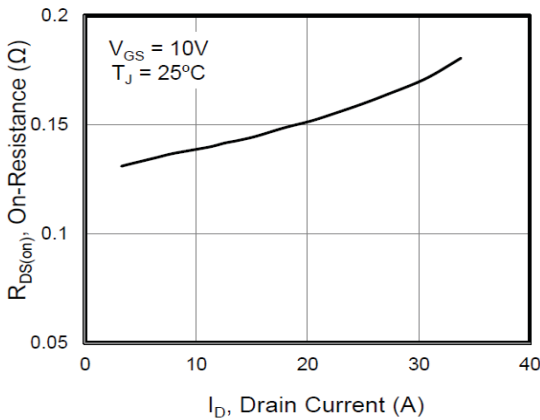


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

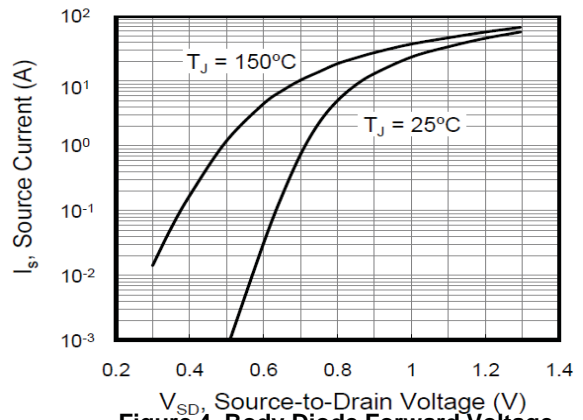


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

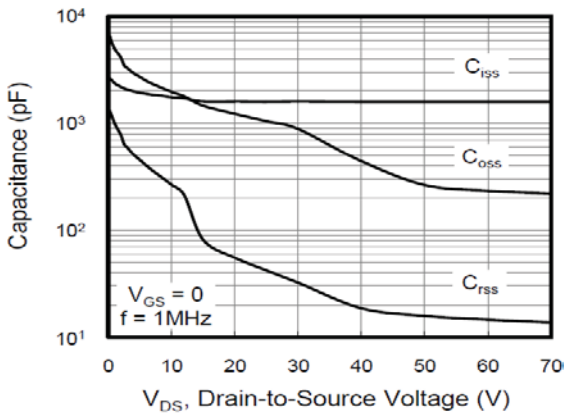


Figure 5. Capacitance Characteristics

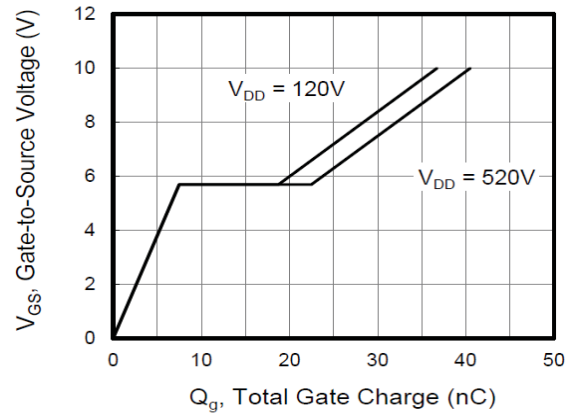


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

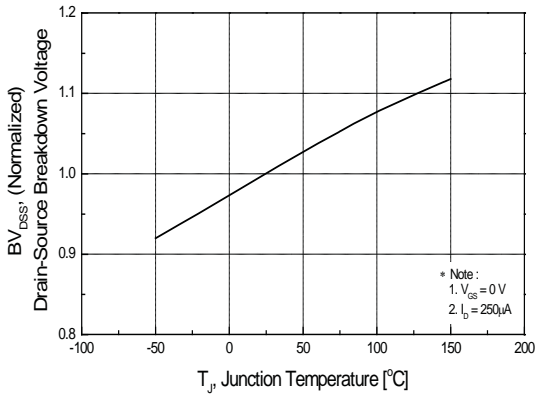


Figure 7. Breakdown Voltage Variation vs Temperature

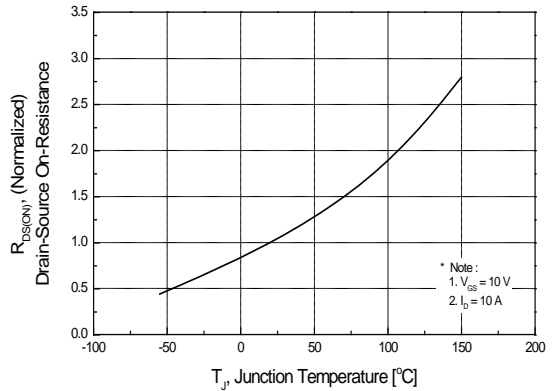


Figure 8. On-Resistance Variation vs Temperature

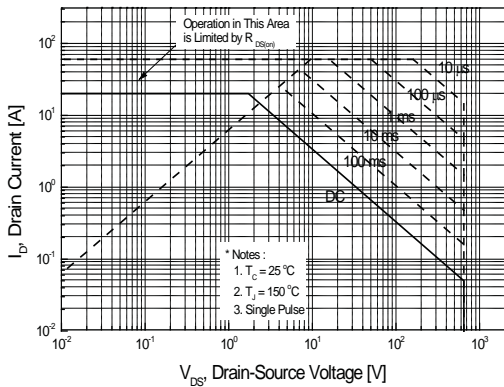


Figure 9. Maximum Safe Operating Area

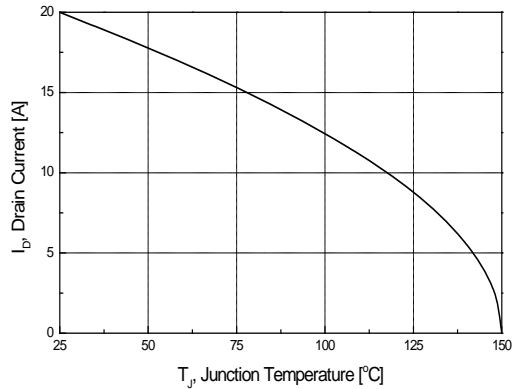


Figure 10. Maximum Drain Current vs Case Temperature

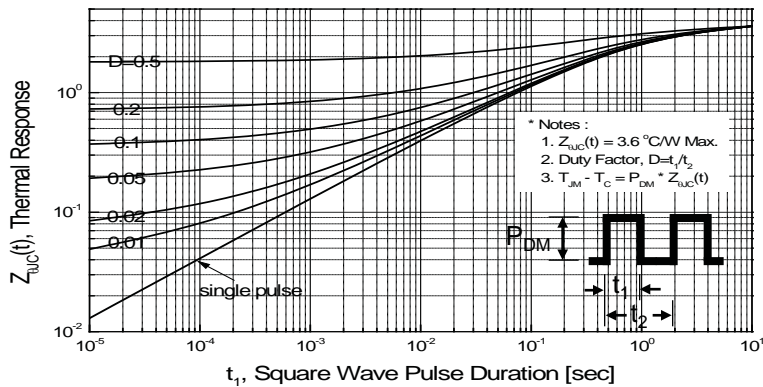


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

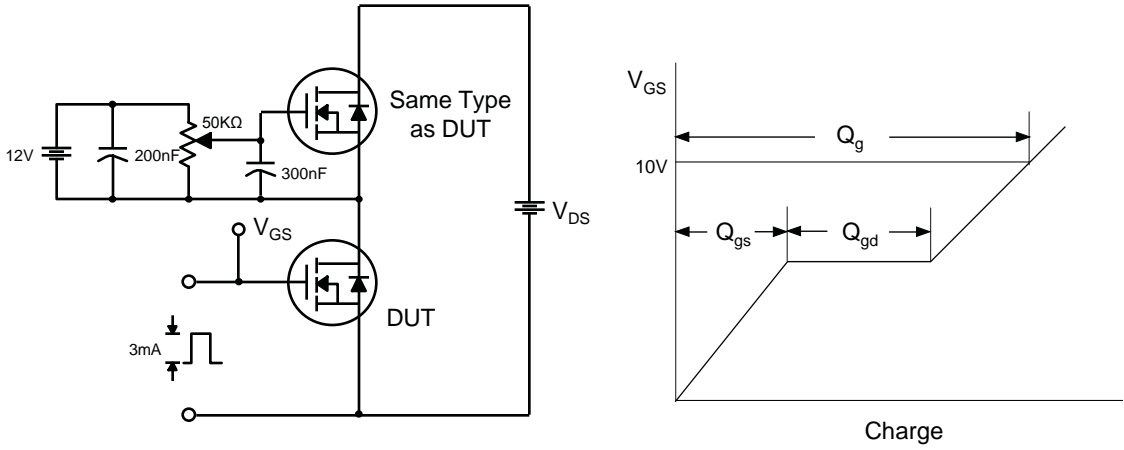


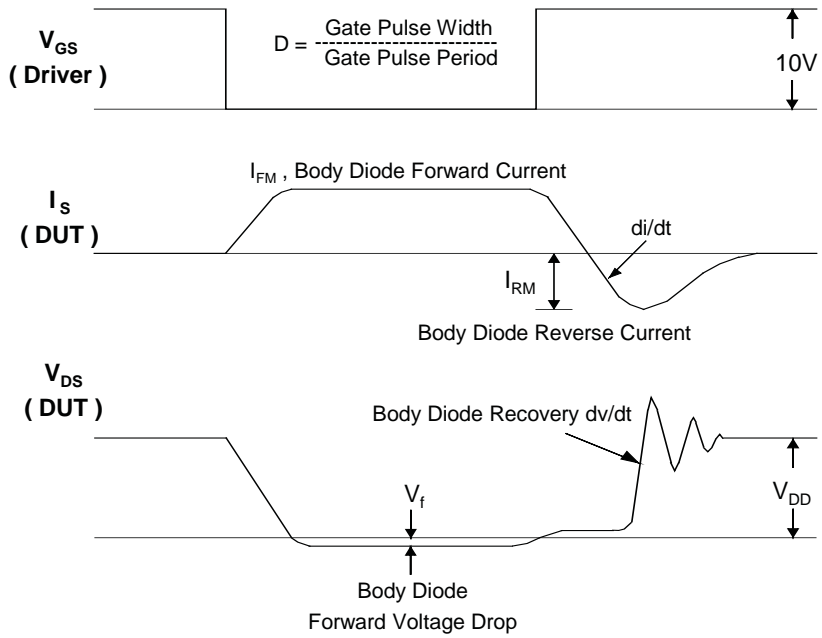
Fig 13. Resistive Switching Test Circuit & Waveforms



Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms



Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

TO-220F

